

## N-channel TrenchMOS logic level FET

Rev. 3 — 11 March 2011

Product data sheet

### 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### **1.3 Applications**

- DC-to-DC converters
- Notebook computers

- Switched-mode power supplies
- Voltage regulators

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	30.4	A
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	6.9	W
Static char	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance		-	3.45	4.4	mΩ
Dynamic c	haracteristics					
Q <sub>GD</sub>	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$	-	7.7	-	nC

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# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source		
3	S	source		
4	G	gate		
5	D	drain		mbb076 S
6	D	drain	SOT96-1 (SO8)	
7	D	drain		
8	D	drain		

# 3. Ordering information

Table 3.	Ordering in	formation		
Type number Packa		Package		
		Name	Description	Version
PHK31NQ	03LT	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

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### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	30.4	A
		$T_{sp} = 100 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	-	17.2	А
I <sub>DM</sub>	peak drain current	T <sub>sp</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <mark>Figure 3</mark>	-	121.8	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	6.9	W
T <sub>stg</sub>	storage temperature		-55	150	°C
Tj	junction temperature		-55	150	°C
Source-dra	in diode				
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C	-	5.7	А
I <sub>SM</sub>	peak source current	$T_{sp} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}$	-	23.1	А
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source	V <sub>GS</sub> = 10 V; T <sub>i(init)</sub> = 25 °C; I <sub>D</sub> = 35 A;	-	120	mJ

LDS(AL)S avalanch

120

80

40

0

Fig 1.

0

50

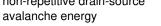
100

 $I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$ 

Normalized continuous drain current as a

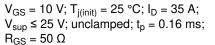
function of mounting base temperature

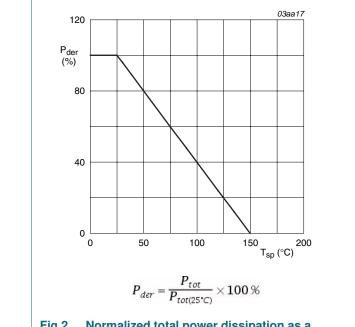
l<sub>der</sub> (%)



03aa25

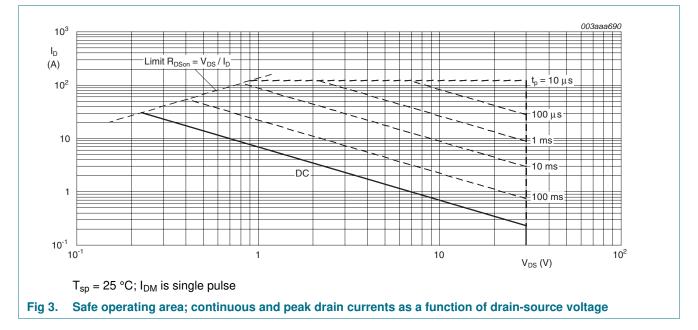
150 200 T<sub>sp</sub> (°C)





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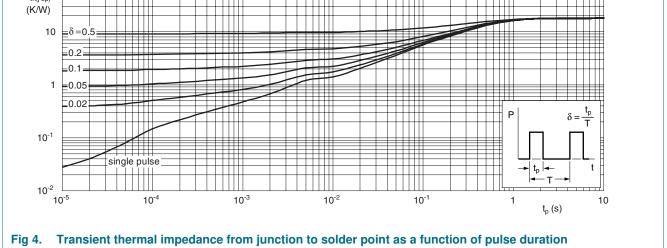
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### 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	18	K/W
10 <sup>2</sup>					003aaa691	
Z <sub>th(j-sp)</sub> (K/W)						



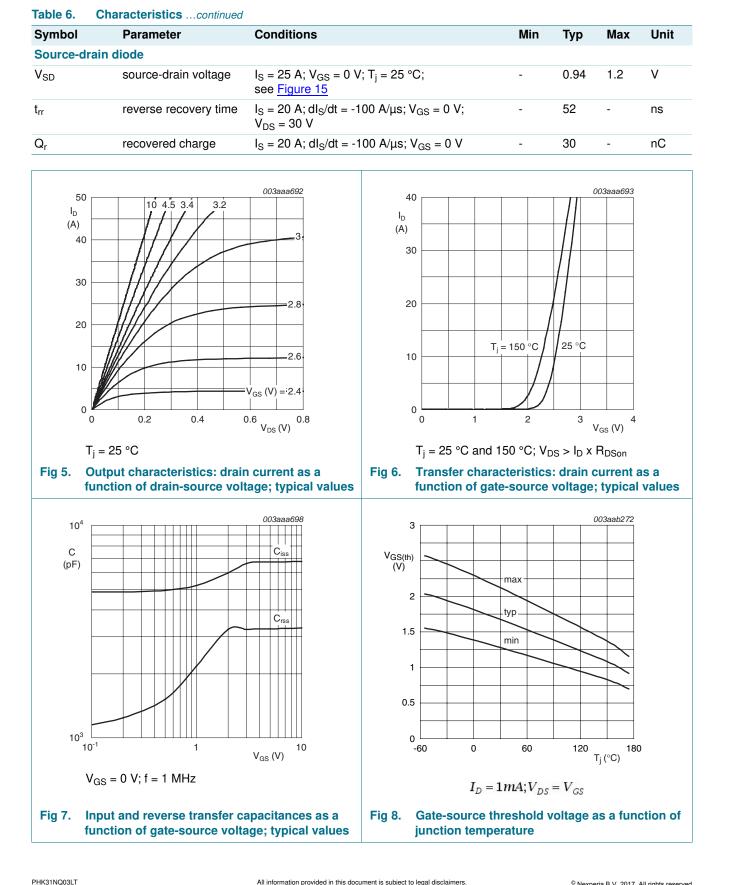
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### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	1.3	1.7	2.15	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	0.8	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 8</u> ; see <u>Figure 9</u>	-	-	2.6	V
IDSS	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	-	3.45	4.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; see <u>Figure 10</u>	-	5.85	7.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	4.25	5.6	mΩ
R <sub>G</sub>	gate resistance	$f = 1 \text{ MHz}; V_{GSS(AC)} = 150 \text{ mV}$	-	1.2	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	33	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 12; see Figure 13	-	13.6	-	nC
Q <sub>GS1</sub>	pre-threshold gate-source charge		-	6.5	-	nC
Q <sub>GS2</sub>	post-threshold gate-source charge		-	7.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	7.7	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; \text{see } \frac{\text{Figure } 12}{12}$	-	2.85	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 0 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C	-	4900	-	pF
		V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	4235	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	840	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	370	-	pF
d(on)	turn-on delay time	$V_{DS}$ = 12 V; $R_L$ = 0.5 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	37	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega$	-	62	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	54	-	ns
t <sub>f</sub>	fall time		-	26	-	ns

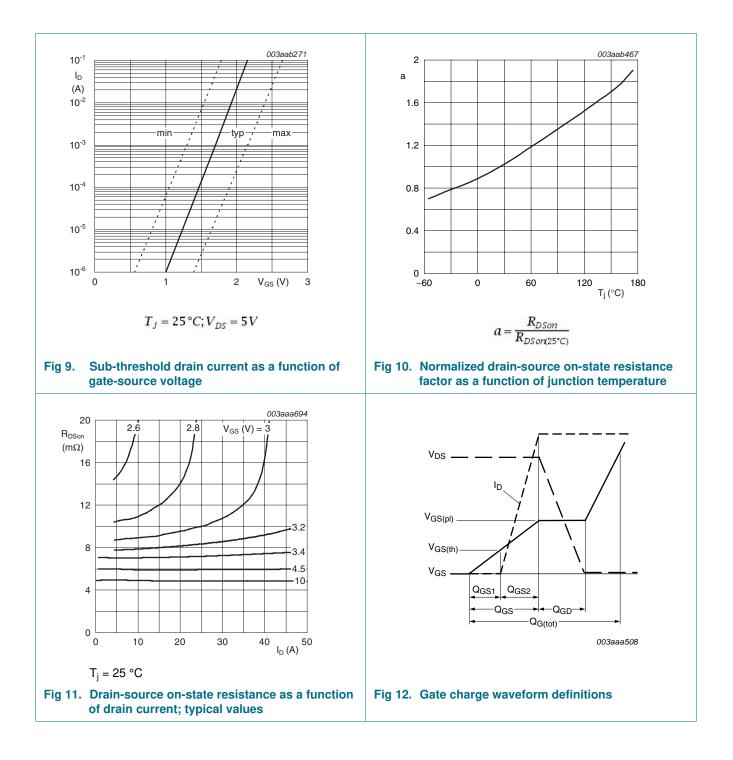
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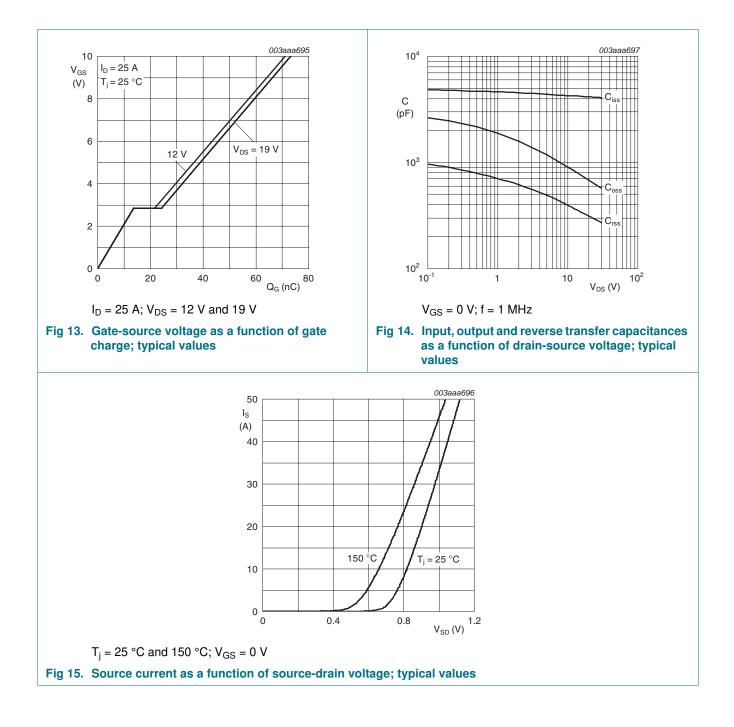
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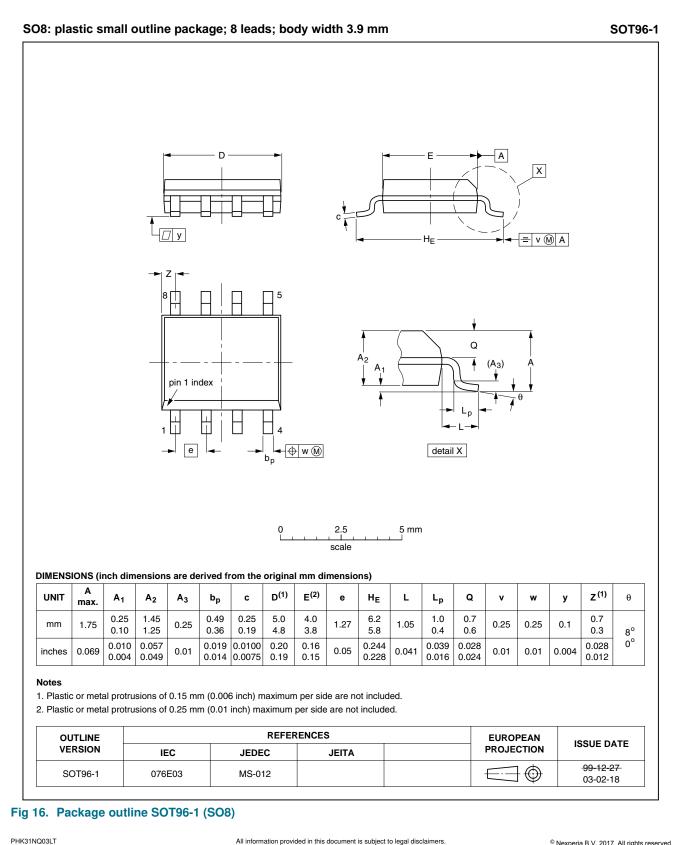
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### 7. Package outline



Product data sheet

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### 8. Revision history

Table 7. Revision I	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHK31NQ03LT v.3	20110311	Product data sheet	-	PHK31NQ03LT v.2
Modifications:	<ul> <li>Various chang</li> </ul>	es to content.		
PHK31NQ03LT v.2	20101220	Product data sheet	-	PHK31NQ03LT v.1

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### 9. Legal information

### 9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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